MICROSTRUCTURE AND MECHANICAL PROPERTIES OF ATOMIC LAYER DEPOSITED ALUMINA DOPED ZIRCONIA

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Tetragonal and cubic ZrO₂ polymorphs, attainable by doping with Al₂O₃, exhibit higher stiffness

and hardness than the otherwise stable monoclinic phase [1]. In this study, ZrO₂ films atomic layer deposited to the thickness of 100 nm were doped by various contents of Al₂O₃ between layers of ZrO₂. The content of Al₂O₃ was between 4.6 and 24.8 mol.% in the films. Undoped ZrO₂ film consisted of a mixture of monoclinic and tetragonal phases, whereas doping with 4.6 mol.% of Al₂O₃ resulted in the stabilization of tetragonal and possibly cubic phases of ZrO₂. Further increase in the content of Al₂O₃ resulted in cubic phase and the appearance of

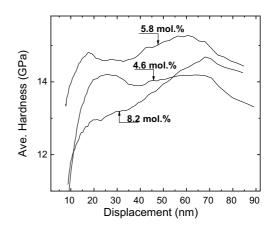


Fig.1 Averaged hardness of 30 indents on the doped crystalline zirconia films with varying amounts of alumina.

amorphous ZrO₂. Mixing ZrO₂ with 12.8 and higher mol.% of Al₂O₃ showed only X-ray amorphous films. All the crystalline films exhibited preferred crystal orientations with extents differing near the substrates and the surface of the films.

The crystalline doped films possessed higher hardness (14 - 15 GPa) compared to the amorphous ones (11 - 12 GPa), while the Young's modulus (165 ± 10 GPa) of the doped films seemed unaffected by the Al₂O₃ content or phase composition. Undoped ZrO₂ film exhibited lower hardness and stiffness than the doped films. The hardness of doped crystalline films increased in the vicinity of the substrate (Fig. 1) even though the hardness of the substrates (12.6 GPa) was lower compared to that of the films. This was explained by the change of preferential crystal orientation near the substrate.

References

1. G. Cousland, X. Cui, A. Smith, A. Stampfl, C. Stampf, 2018, J. Phys. Chem. Solids, 122, 52

